



COPY OF PAPERS
ORIGINALLY FILED

Attorney's Docket No. 42390P5769

#17D
Amdd
SDavis
7/12/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

GANG BAI

Serial No. 09/109,261

Filed: June 30, 1998

For: A MULTI-LAYER GATE DIELECTRIC

Examiner: Warren, M.

Art Group: 2815

AMENDMENT AND RESPONSE TO OFFICE ACTION

Box Non-Fee Amendment
Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the Office Action mailed March 13, 2002, in connection with the above-referenced patent application, the Applicant respectfully requests entry of the following amendments and requests reconsideration in view of the following remarks.

IN THE CLAIMS

Presented below are all the amended claims in clean unmarked form. The claims in marked-up form are presented as an attachment.

8. (Four Times Amended) A transistor device having a gate electrode overlying a gate dielectric formed directly on a semiconductor substrate, the gate dielectric comprising:
- a first dielectric material having a first dielectric constant;
 - a second dielectric material having a second dielectric constant different from the first dielectric constant; and
 - the first and second dielectric materials being scalable for a feature size technology having a gate length in the range of 25-150nm.